Quad buffer/line driver; 3-state Rev. 4 — 10 January 2013

Product data sheet

General description 1.

The 74HC125; 74HCT125 is a quad buffer/line driver with 3-state outputs controlled by the output enable inputs (nOE). A HIGH on nOE causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

Features and benefits 2.

- Complies with JEDEC standard no. 7A
- Input levels:
 - The 74HC125: CMOS levels
 - The 74HCT125: TTL levels
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Ordering information 3.

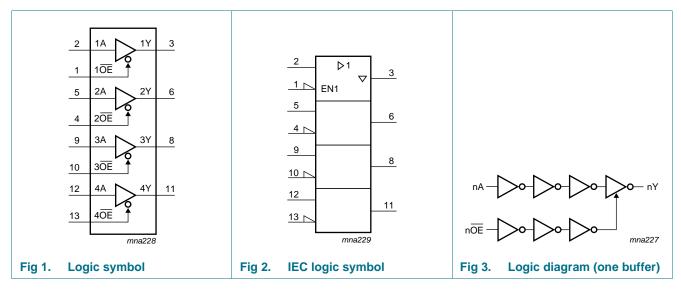
Table 1. **Ordering information**

Type number	Package			
	Temperature range	Name	Description	Version
74HC125N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT125N				
74HC125D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1
74HCT125D			3.9 mm	
74HC125DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1
74HCT125DB			width 5.3 mm	
74HC125PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body	SOT402-1
74HCT125PW			width 4.4 mm	



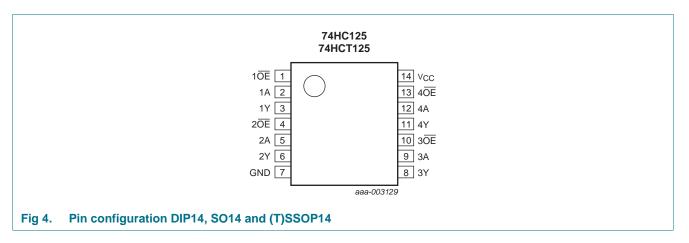
Quad buffer/line driver; 3-state

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.Pin description	n	
Symbol	Pin	Description
$1\overline{OE}$, $2\overline{OE}$, $3\overline{OE}$, $4\overline{OE}$	1, 4, 10, 13	output enable input (active LOW)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table ^[1]		
Control	Input	Output
n <mark>OE</mark>	nA	nY
L	L	L
	Н	Н
Н	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

Limiting values 7.

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$V_{\rm O} = -0.5 \text{ V}$ to ($V_{\rm CC}$ + 0.5 V)	-	±35	mA
I _{CC}	supply current		-	+70	mA
I _{GND}	ground current		-	-70	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2]		
	DIP14 package		-	750	mW
	SO14 and (T)SSOP14 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C. For SO14 package: Ptot derates linearly with 8 mW/K above 70 °C. For (T)SSOP14 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter		74HC ²	125		74HC	74HCT125		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC12	5									
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = –20 $\mu A; V_{CC}$ = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = 20 μ A; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{OZ}	OFF-state output current		-	-	±0.5	-	±5.0	-	±10.0	μΑ

Quad buffer/line driver; 3-state

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	8.0	-	80	-	160	μA
CI	input capacitance		-	3.5	-					pF
74HCT1	25									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
output	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 6.0 \text{ mA}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	$ V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 5.5 \text{ V}; $	-	-	±0.5	-	±5.0	-	±10	μA
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μA
∆I _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; $I_O = 0$ A; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V	-	100	360	-	450	-	490	μΑ
Cı	input capacitance		-	3.5	-					pF

Quad buffer/line driver; 3-state

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74HC125										
t _{pd}	propagation	nA to nY; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 2.0 V$		-	30	100	-	125	-	150	ns
		$V_{CC} = 4.5 V$		-	11	20	-	25	-	30	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	9	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	9	17	-	21	-	26	ns
t _{en}	enable time	nOE to nY; see Figure 6	[2]								
		$V_{CC} = 2.0 V$		-	41	125	-	155	-	190	ns
		$V_{CC} = 4.5 V$		-	15	25	-	31	-	38	ns
		$V_{CC} = 6.0 V$		-	12	21	-	26	-	32	ns
t _{dis}	disable time	nOE to nY; see Figure 6	[3]								
		$V_{CC} = 2.0 V$		-	41	125	-	155	-	190	ns
		$V_{CC} = 4.5 V$		-	15	25	-	31	-	38	ns
		$V_{CC} = 6.0 V$		-	12	21	-	26	-	32	ns
t _t	transition	nY; see <u>Figure 5</u>	<u>[4]</u>								
	time	$V_{CC} = 2.0 V$		-	14	60	-	75	-	90	ns
		$V_{CC} = 4.5 V$		-	5	12	-	15	-	18	ns
		$V_{CC} = 6.0 V$		-	4	10	-	13	-	15	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	<u>[5]</u>	-	22	-	-	-	-	-	pF

Quad buffer/line driver; 3-state

Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C t	o +125 °C	Unit	
				Min	Тур	Max	Min	Max	Min	Max	
For type	74HCT125					•					
t _{pd}	propagation	nA to nY; see Figure 5	[1]								
	delay	$V_{CC} = 4.5 V$		-	15	25	-	31	-	38	ns
		$V_{CC} = 5 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	12	-	-	-	-	-	ns
t _{en}	enable time	nOE to nY; see Figure 6	[2]								
		$V_{CC} = 4.5 V$		-	15	28	-	35	-	42	ns
t _{dis}	disable time	nOE to nY; see Figure 6	[3]								
		$V_{CC} = 4.5 V$		-	15	25	-	31	-	38	ns
t _t	transition time	nY; see <u>Figure 5</u>	<u>[4]</u>	-	5	12	-	15	-	18	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	<u>[5]</u>	-	24	-	-	-	-	-	pF

Table 7. Dynamic characteristics ... continued

FO a Frankson attended and a state for the track size of Figure 7 010.0 11-11-

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_{en} is the same as t_{PZH} and t_{PZL} .

[3] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[4] t_t is the same as t_{THL} and t_{TLH} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

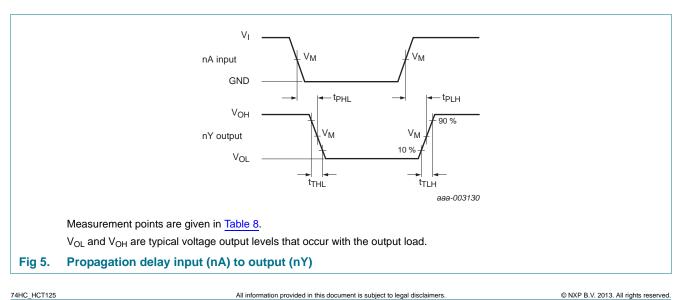
 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



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74HC125; 74HCT125

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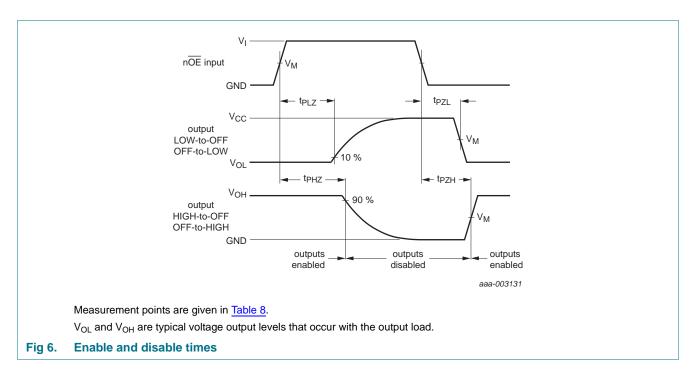


Table 8.Measurement points

Туре	Input	Output
	V _M	V _M
74HC125	0.5V _{CC}	0.5V _{CC}
74HCT125	1.3 V	1.3 V

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74HC125; 74HCT125

Quad buffer/line driver; 3-state

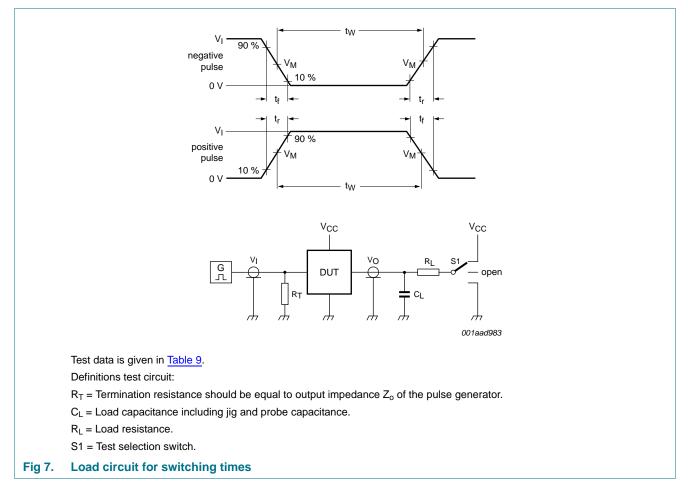


Table 9. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74HC125	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74HCT125	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

Quad buffer/line driver; 3-state

12. Package outline

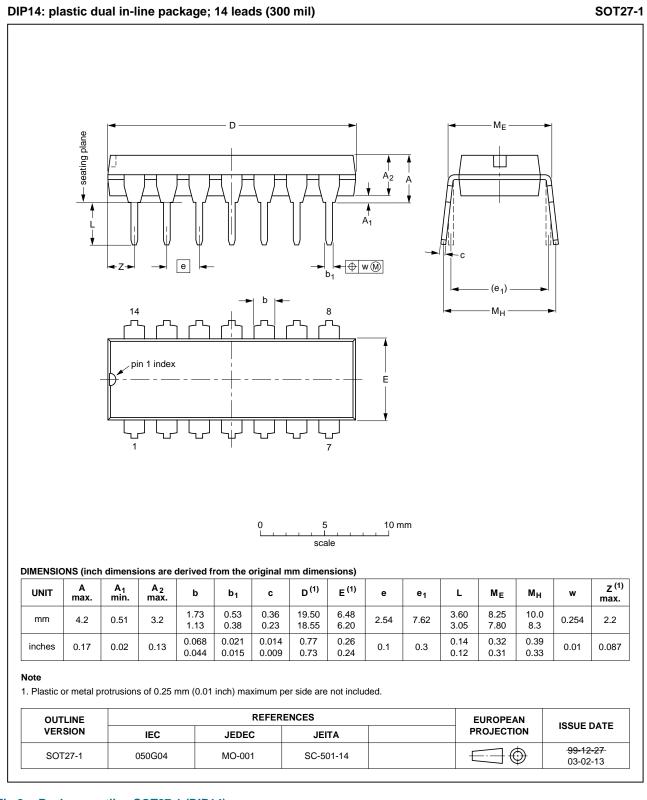


Fig 8. Package outline SOT27-1 (DIP14)

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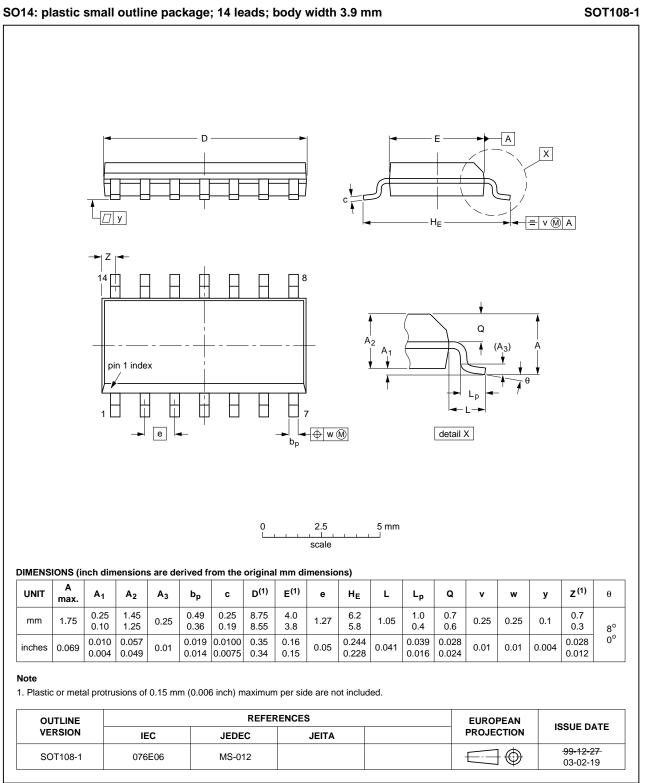


Fig 9. Package outline SOT108-1 (SO14)

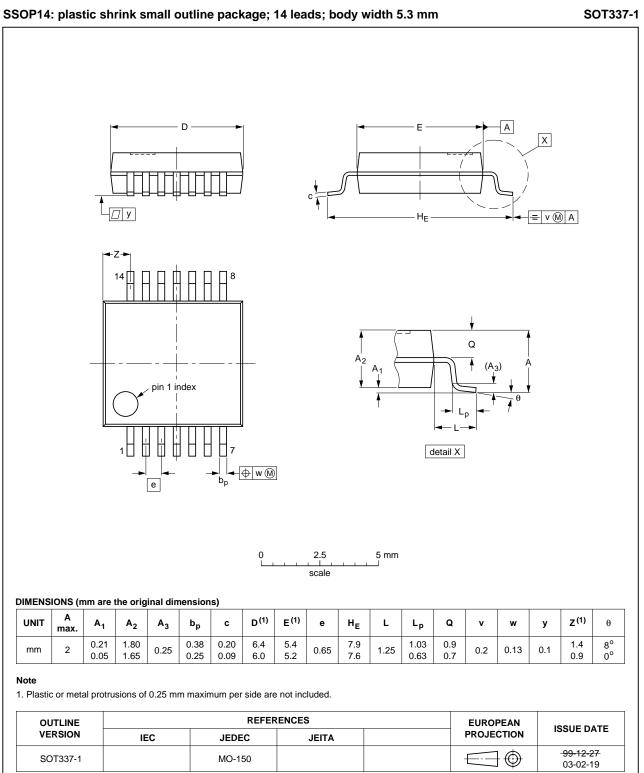


Fig 10. Package outline SOT337-1 (SSOP14)

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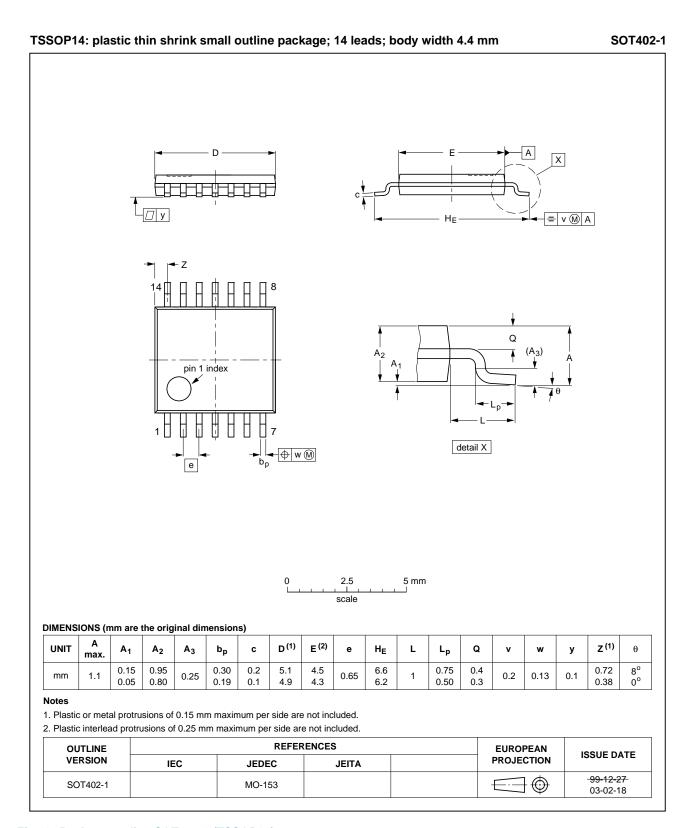


Fig 11. Package outline SOT402-1 (TSSOP14)

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13. Abbreviations

AcronymDescriptionCMOSComplementary Metal Oxide SemiconductorLSTTLLow-power Schottky Transistor-Transistor LogicESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelCDMCharge-Device ModelTTLTransistor-Transistor Logic	Table 10.	Abbreviations
LSTTLLow-power Schottky Transistor-Transistor LogicESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelCDMCharge-Device Model	Acronym	Description
ESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelCDMCharge-Device Model	CMOS	Complementary Metal Oxide Semiconductor
HBM Human Body Model MM Machine Model CDM Charge-Device Model	LSTTL	Low-power Schottky Transistor-Transistor Logic
MM Machine Model CDM Charge-Device Model	ESD	ElectroStatic Discharge
CDM Charge-Device Model	HBM	Human Body Model
	MM	Machine Model
TTL Transistor-Transistor Logic	CDM	Charge-Device Model
	TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history **Document ID Release date** Data sheet status Change notice Supersedes 74HC_HCT125 v.4 20130110 Product data sheet 74HC_HCT125 v.3 -Modifications: • New general description. 74HC HCT125 v.3 20120827 Product data sheet 74HC_HCT125_CNV v.2 -Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. 74HC_HCT125_CNV v.2 19970827 Product data sheet _ -

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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17. Contents

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Date of release: 10 January 2013 Document identifier: 74HC_HCT125